

Schottky Barrier Diode

F1J2E

Features

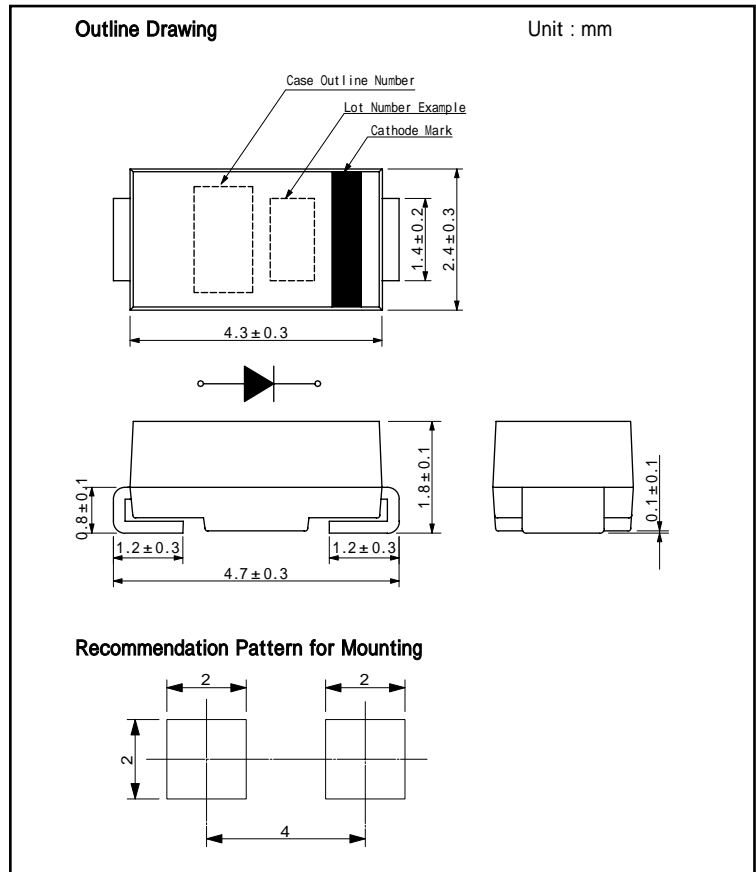
- Small and thin package
- Various kinds
- Taping capable of high density mounting

Applications

- HIC
- High-frequency rectification
- Switching regulations
- Mounting for both sides printed circuit board
- Preventing power supply from counter-flowing.
- Avoiding reverse current wrong setting of a battery.

Structures

- Resin molded, and Silicon Schottky Barrier Diode.
- Marking symbol : [J2E]
- Weight : 0.07g
- Terminal plating : Sn
- Conforms to RoHS regulations



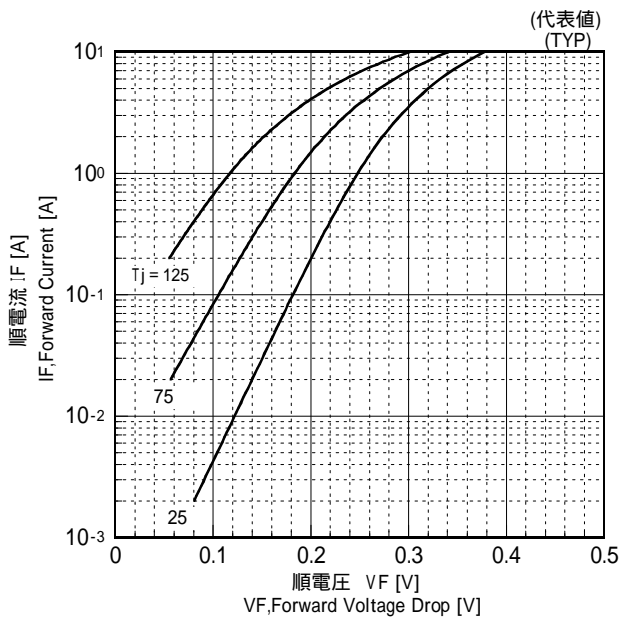
Absolute Maximum Ratings (Ta=25)

Items	Symbol	Conditions	Ratings	Unit
Repetitive Peak Reverse Voltage	V_{RM}		20	V
Non-Repetitive Peak Reverse Voltage	V_{RSM}		25	V
Average Rectified Forward Current	I_O	Ta=25 , Half sin wave 180 ° ,Resistive Load	2	A
Peak Forward Surge Current	I_{FSM}	Tj=25 , 50Hz, Single-phase, Half sin wave, Non-Repetitive	30	A
Operating Junction Temperature	T_j		-40 ~ +125	
Storage Temperature	T_{stg}		-40 ~ +125	

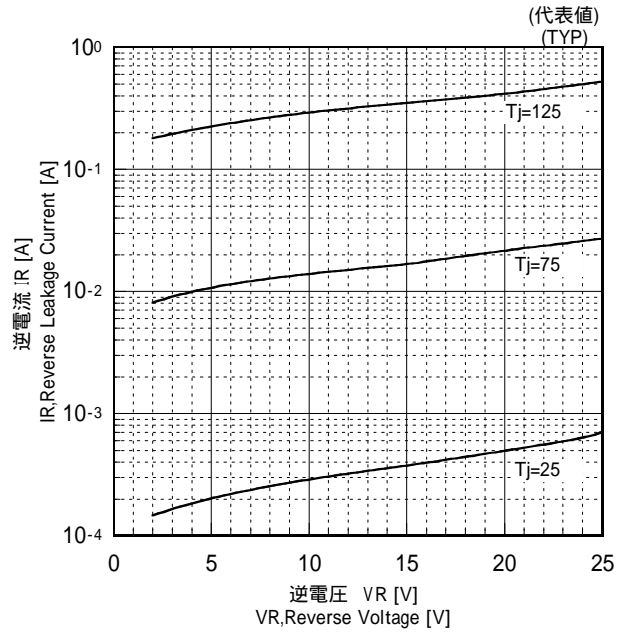
Electrical Characteristics (Tj=25)

Items	Symbol	Conditions	TYP.	MAX.	Unit
Forward Voltage Drop	V_{F1}	$I_f=1A$	250	-	mV
	V_{F2}	$I_f=2A$	270	300	mV
Reverse Leakage Current	i_R	$V_R=20V$	-	2.0	mA
Thermal resistance (junction to ambient)	Rth(j-a)	Glass Epoxy Substrate	-	157	/W
		Alumina Substrate	-	108	/W

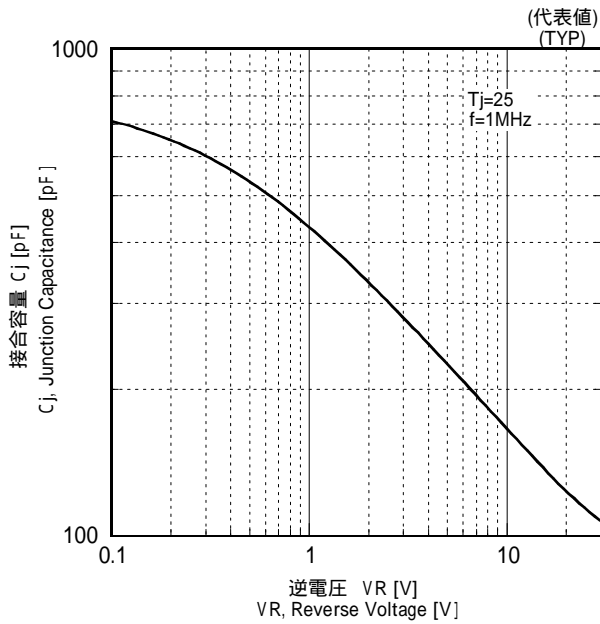
Characteristics Diagrams



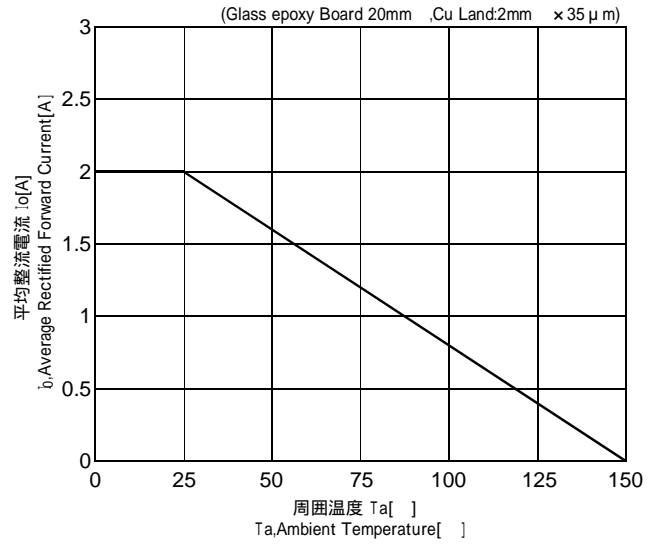
FORWARD CHARACTERISTICS



REVERSE CHARACTERISTICS



TYPICAL JUNCTION CAPACITANCE



AVERAGE RECTIFIED FORWARD CURRENT